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CONTENTS

Classical semiconductors

Investigations on synthesis, growth, electrical and defect studies of lithium selenoindate single crystals
P. Vijayakumar, M. Magesh, A. Arunkumar, G. Anandha Babu, P. Ramasamy and S. Abhaya 17

Growth of Ga- and N-polar GaN layers on O face ZnO substrates by molecular beam epitaxy
Y. Xia, J. Brault, P. Vennéguès, M. Nemoz, M. Teisseire, M. Leroux and J.-M. Chauveau 35

Structure and composition analysis of the Cu–Zn–Se ternary compounds by TEM/EDS
T.-M. Chen, S.-M. Lan, W.-Y. Uen, T.-N. Yang and K.-J. Chang 87

Strained InGaAs/InAlAs quantum wells for complementary III–V transistors
B.R. Bennett, T.F. Chick, J.B. Boos, J.G. Champlain and A.A. Podpirka 92

Novel activation process for Mg-implanted GaN
S. Hashimoto, T. Nakamura, Y. Honda and H. Amano 112

Unveiling transient GaAs/GaP nanowire growth behavior using group V oscillations
J.P. Boulanger and R.R. LaPierre 116

Highly uniform growth of 2-inch GaN wafers with a multi-wafer HVPE system
N. Liu, J. Wu, W. Li, R. Luo, Y. Tong and G. Zhang 132

Electronic materials

Growth of a Si_{0.50}Ge_{0.50} crystal by the traveling liquidus-zone (TLZ) method in microgravity
K. Kinoshita, Y. Arai, Y. Inatomi, T. Tsukada, S. Adachi, H. Miyata, R. Tanaka, J. Yoshikawa, T. Kihara, H. Tomioka, H. Shibayama, Y. Kubota, Y. Warashina, Y. Sasaki, Y. Ishizuka, Y. Harada, S. Wada, C. Harada, T. Ito, M. Takayanagi and S. Yoda 12

Onset of plastic relaxation in semipolar (11 $\bar{2}$ 2) In_xGa_{1-x}N/GaN heterostructures
I.L. Koslow, M.T. Hardy, P. Shan Hsu, F. Wu, A.E. Romanov, E.C. Young, S. Nakamura, S.P. DenBaars and J.S. Speck 48

A novel crystal growth technique from the melt: Levitation-Assisted Self-Seeding Crystal Growth Method
Z. Galazka, R. Uecker and R. Fornari 61

Formation of dendritic crystal structures in thin silicon films on silicon dioxide by carbon ion implantation and high intensity large area flash lamp irradiation
M. Voelskow, R. Endler, T. Schumann, A. Mücklich, X. Ou, E.H. Liepack, T. Gebel, A. Peeva and W. Skorupa 70

Low dislocation density AlGaN epilayers by epitaxial overgrowth of patterned templates
A.A. Allerman, M.H. Crawford, S.R. Lee and B.G. Clark 76

Solution growth; industrial biological and molecular crystallization

γ -CuI crystal growth in ionic liquids by the oxygen-free cooling method
B. Lou, J. Zhang, H. Luo, J. Pan and J. Pan 1

Growth and FIB-SEM analyses of C₆₀ microtubes vertically synthesized on porous alumina membranes
K. Miyazawa, R. Kuriyama, S. Shimomura, T. Wakahara and M. Tachibana 5

An in situ AFM investigation on the morphology of the (100) growth interface of ZTS crystal
Y. Cao, M. Li, M. Cheng, J. Song and Z. Hu 22

Improvement of growth rate and optical performances of rapidly grown KDP crystal by adding cyclohexane diamine tetraacetic acid in growth solution
S. Zhu, S. Wang, J. Ding, G. Liu, W. Liu, L. Liu, D. Wang, W. Li, Q. Gu and X. Xu 98

Contents continued on inside back cover



Contents continued from outside back cover

Undercooling growth and magnetic characterization of ferromagnetic shape memory alloy Ni_2FeGa single crystals J.F. Qian, H.G. Zhang, J.L. Chen, W.H. Wang and G.H. Wu	107	Single crystal flux growth of the Ising spin-chain system $\gamma\text{-CoV}_2\text{O}_6$ Z. He and M. Itoh	103
Studies on the structure, growth and characterization of morpholinium perchlorate single crystals A. Arunkumar and P. Ramasamy	124	Origins of unintentional incorporation of gallium in AlInN layers during epitaxial growth, part I: Growth of AlInN on AlN and effects of prior coating S. Choi, H. Jin Kim, Z. Lochner, J. Kim, R.D. Dupuis, A.M. Fischer, R. Juday, Y. Huang, T. Li, J.Y. Huang, F.A. Ponce and J.-H. Ryou	137
General subjects		Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions J. Kim, Z. Lochner, M.-H. Ji, S. Choi, H.J. Kim, J.S. Kim, R.D. Dupuis, A.M. Fischer, R. Juday, Y. Huang, T. Li, J.Y. Huang, F.A. Ponce and J.-H. Ryou	143
Effect of crucible shape on heat transport and melt-crystal interface during the Kyropoulos sapphire crystal growth C. Chen, H.J. Chen, W.B. Yan, C.H. Min, H.Q. Yu, Y.M. Wang, P. Cheng and C.C. Liu	29	Corrigendum to "Cross-sectional X-ray microdiffraction study of a thick AlN film grown on a trench-patterned AlN/ $\alpha\text{-Al}_2\text{O}_3$ template" [J. Cryst. Growth 381 (2013) 37–42, doi: 10.1016/j.jcrysgro.2013.07.012] D.T. Khan, S. Takeuchi, J. Kikkawa, Y. Nakamura, H. Miyake, K. Hiramatsu, Y. Imai, S. Kimura, O. Sakata and A. Sakai	150
Numerical and experimental studies on the Black Periphery Wafer in CZ Si growth W. Su, R. Zuo, J. Lu, C. Di and X. Cheng	42		
Single crystal growth of the hexagonal manganites $R\text{MnO}_3$ (R =rare earth) by the optical floating-zone method C. Fan, Z.Y. Zhao, J.D. Song, J.C. Wu, F.B. Zhang and X.F. Sun	54		
Crystal growth, characterization of NdTaO_4 : A new promising stoichiometric neodymium laser material K. Ning, Q. Zhang, D. Zhang, J. Fan, D. Sun, X. Wang and Y. Hang	83		